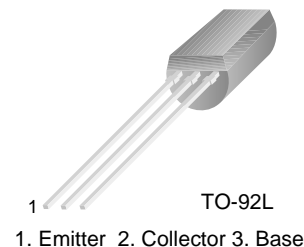


■■ APPLICATION: High Current Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CB0</sub>	30	V
Collector-emitter voltage	V <sub>CEO</sub>	30	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>C</sub>	2	A
Collector Power Dissipation	P <sub>C</sub>	1	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h <sub>FE</sub>	100		320		V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA
Collector Cut-off Current	I <sub>CB0</sub>			0.1	μA	V <sub>CB</sub> = 30V, I <sub>E</sub> =0
Emitter Cut-off Current	I <sub>EBO</sub>			0.1	μA	V <sub>EB</sub> = 5V, I <sub>C</sub> =0
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	30			V	I <sub>C</sub> = 0.1mA, I <sub>E</sub> =0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	30			V	I <sub>C</sub> = 10mA, I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5			V	I <sub>E</sub> = 0.1mA, I <sub>C</sub> =0
Base-Emitter Voltage	V <sub>BE</sub>			1.0	V	V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			2.0	V	I <sub>C</sub> = 1.5A, I <sub>B</sub> = 30mA
Gain bandwidth product	f <sub>T</sub>		120		MHz	I <sub>C</sub> = 500mA, V <sub>CE</sub> = 2V
Common Base Output Capacitance	C <sub>ob</sub>		13		PF	V <sub>CB</sub> = 10V, I <sub>E</sub> =0, f=1MHz

■■ h<sub>FE</sub> Classification And Marking

Classification	O	Y
h <sub>FE</sub>	100~200	160~320